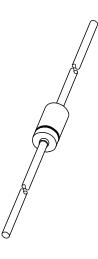
DISCRETE SEMICONDUCTORS

DATA SHEET



1N4531; 1N4532 High-speed diodes

Product specification Supersedes data of April 1992 File under Discrete Semiconductors, SC01 1996 Apr 03





High-speed diodes

1N4531; 1N4532

FEATURES

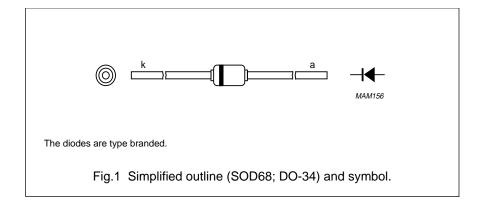
- Hermetically sealed leaded glass SOD68 (DO-34) package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 75 V
- Repetitive peak forward current: max. 450 mA
- Forward voltage: max. 1 V.

APPLICATIONS

- · High-speed switching
- Protection diodes in reed relays.

DESCRIPTION

The 1N4531, 1N4532 are high-speed switching diodes fabricated in planar technology, and encapsulated in hermetically sealed leaded glass SOD68 (DO-34) packages.



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------------|---|------|------|------|
| V _{RRM} | repetitive peak reverse voltage | | _ | 75 | V |
| V_R | continuous reverse voltage | | _ | 75 | ٧ |
| I _F | continuous forward current | see Fig.2 | _ | 200 | mA |
| I _{FRM} | repetitive peak forward current | | _ | 450 | mA |
| I _{FSM} | non-repetitive peak forward current | square wave; T _j = 25 °C prior to surge; see Fig.4 | | | |
| | | t = 1 μs | _ | 4 | A |
| | | t = 1 ms | _ | 1 | A |
| | | t = 1 s | _ | 0.5 | A |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | _ | 500 | mW |
| T _{stg} | storage temperature | | -65 | +200 | °C |
| Tj | junction temperature | | _ | 200 | °C |

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ELECTRICAL CHARACTERISTICS

 $T_i = 25$ °C; unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-----------------|--------------------------|--|------|------|------|
| V _F | forward voltage | I _F = 10 mA; see Fig.3 | _ | 1000 | mV |
| I _R | reverse current | see Fig.5 | | | |
| | IN4531 | V _R = 20 V | _ | 25 | nA |
| | | V _R = 20 V; T _j = 150 °C | _ | 50 | μΑ |
| | IN4532 | V _R = 50 V | _ | 100 | nA |
| | | V _R = 50 V; T _j = 150 °C | _ | 100 | μΑ |
| C _d | diode capacitance | f = 1 MHz; V _R = 0; see Fig.6 | | | |
| | IN4531 | | _ | 4 | pF |
| | IN4532 | | _ | 2 | pF |
| t _{rr} | reverse recovery time | when switched from I _F = 10 mA to | | | |
| | IN4531 | $I_R = 60 \text{ mA}; R_L = 100 \Omega;$ | _ | 4 | ns |
| | IN4532 | measured at I _R = 1 mA; see Fig.7 | _ | 2 | ns |
| | reverse recovery time | when switched from I _F = 10 mA to | | | |
| | IN4532 | I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.7 | _ | 4 | ns |
| V _{fr} | forward recovery voltage | when switched from $I_F = 100$ mA; $t_r \le 30$ ns; see Fig.8 | _ | 3 | V |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|----------------------|---|--------------------------|-------|------|
| R _{th j-tp} | thermal resistance from junction to tie-point | lead length 5 mm | 120 | K/W |
| R _{th j-a} | thermal resistance from junction to ambient | lead length 5 mm; note 1 | 350 | K/W |

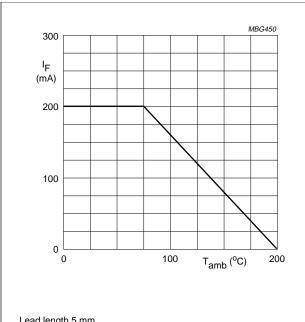
Note

1. Device mounted on a printed circuit-board without metallization pad.

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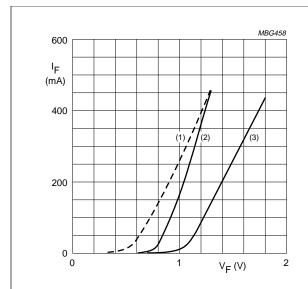
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GRAPHICAL DATA



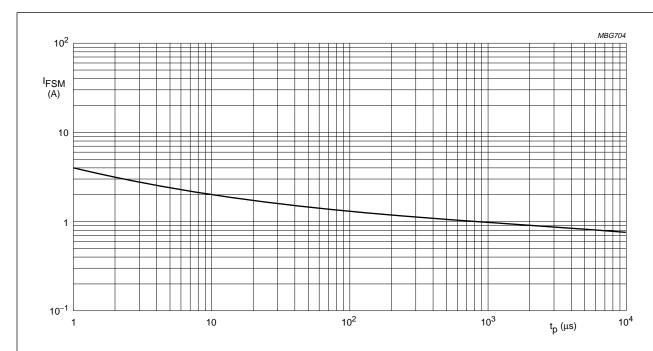
Lead length 5 mm.

Maximum permissible continuous forward current as a function of ambient temperature.



- (1) $T_i = 175$ °C; typical values.
- (2) $T_j = 25$ °C; typical values.
- (3) $T_j = 25$ °C; maximum values.

Forward current as a function of forward voltage.



Based on square wave currents.

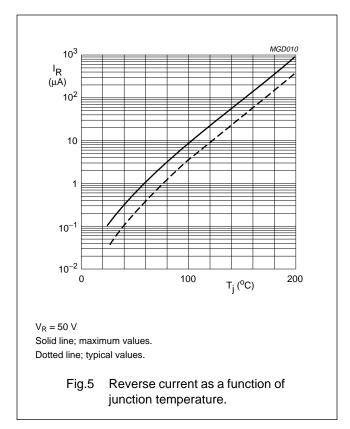
 $T_j = 25$ °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

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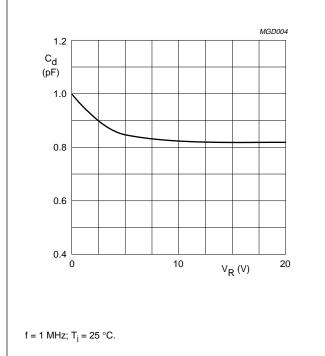
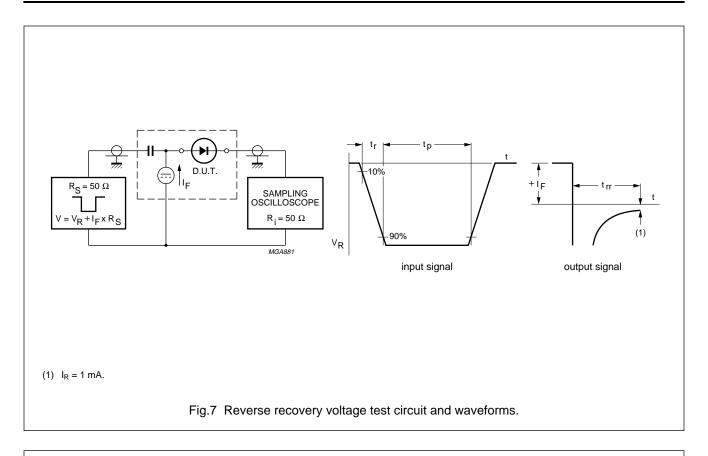
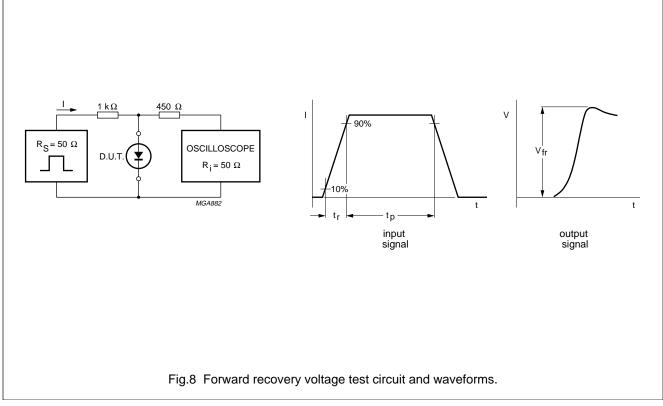


Fig.6 Diode capacitance as a function of reverse voltage; typical values.

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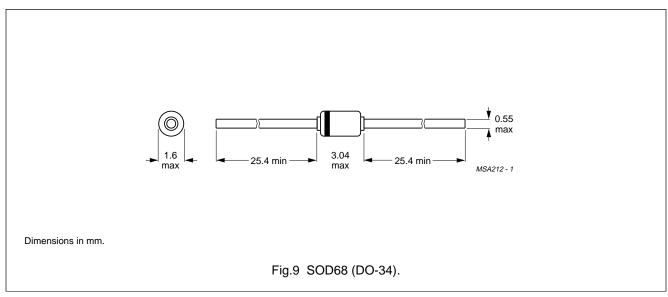




High-speed diodes

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PACKAGE OUTLINE



DEFINITIONS

| Data Sheet Status | |
|---------------------------|---|
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.